

Midterm Exam (20%)

ENEE 359a: Digital VLSI Design, Spring 2007

The Ides of March, Opening Round of the NCAA Tournament

This exam should take you less than an hour: 5 questions, 10 minutes apiece. The exam is closed book, closed notes.

Note that each question is worth the same number of points; this means you should do those questions you find easy first.

Solutions

Name: _____

Score:

Problem 1:	out of 4
Problem 2:	out of 4
Problem 3:	out of 4
Problem 4:	out of 4
Problem 5:	out of 4
Total:	

Grade Distribution:

20 - X X

19 - X X X X

18 - X X X

17 -

16 - X

15 - X X X

14 -

13 - X

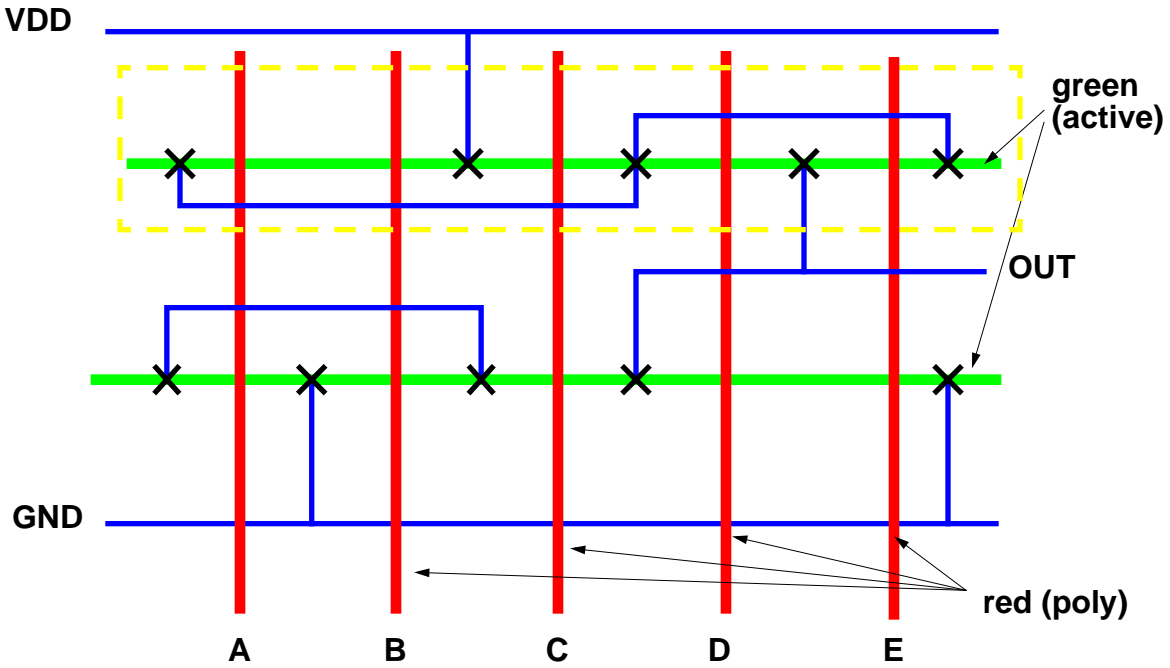
12 -

11 -

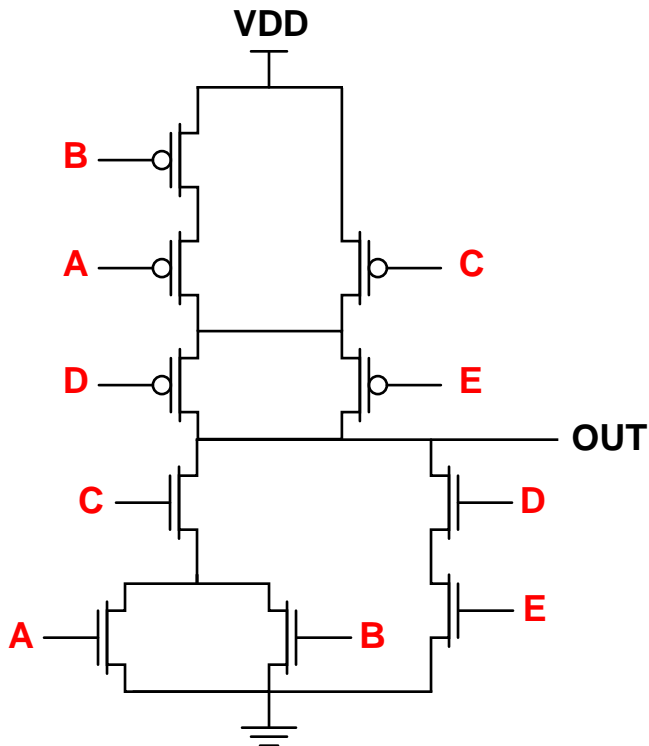
10 -

9 - X

1. Consider the following stick diagram. Draw the electrically equivalent transistor-level schematic. What logic equation does the circuit implement?



solution:

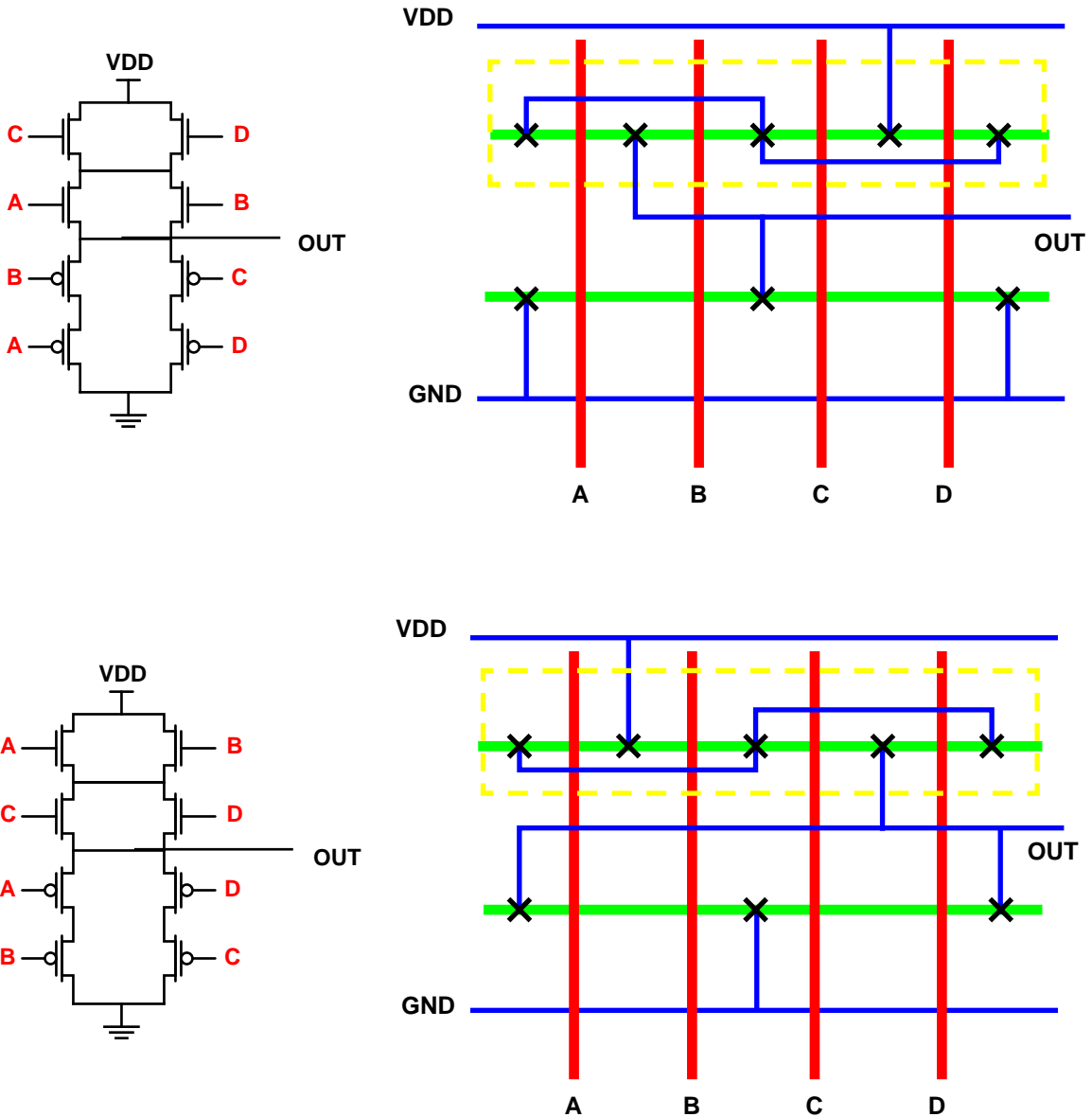


$$\text{out} = \sim(\text{DE} + \text{C}(\text{A}+\text{B}))$$

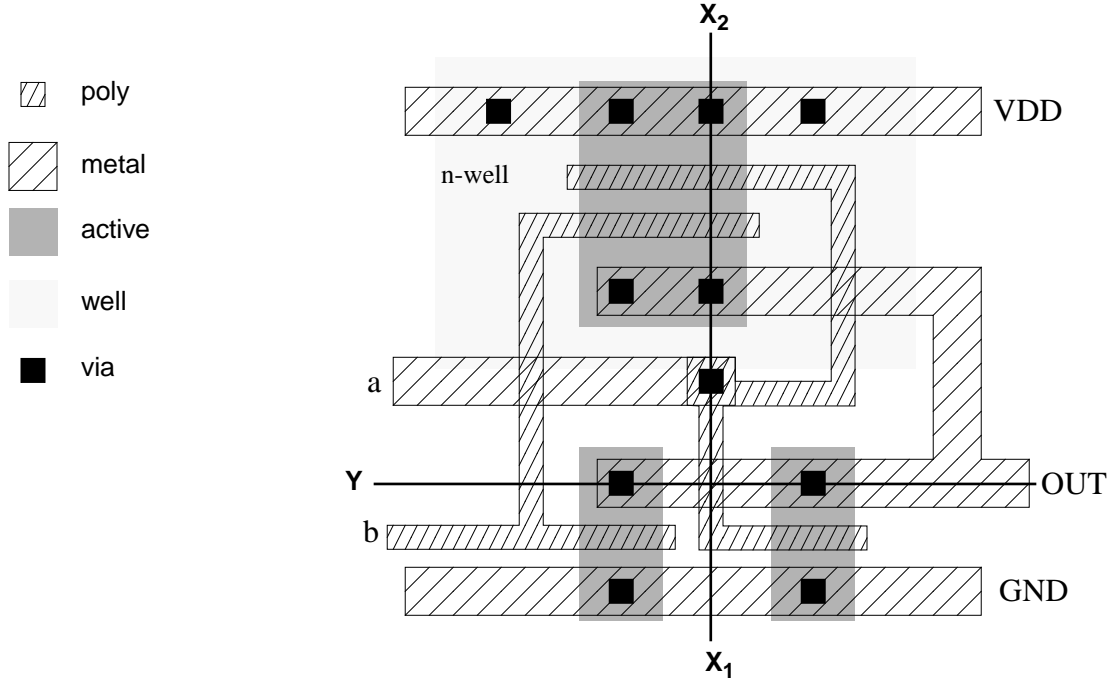
$$\text{out} = \sim(\text{DE} + \text{CA} + \text{CB})$$

2. Consider the logical expression $out = \sim(ab + cd)$. Convert this to a schematic diagram for static CMOS logic, then convert it to a stick-diagram layout (as in question 1).

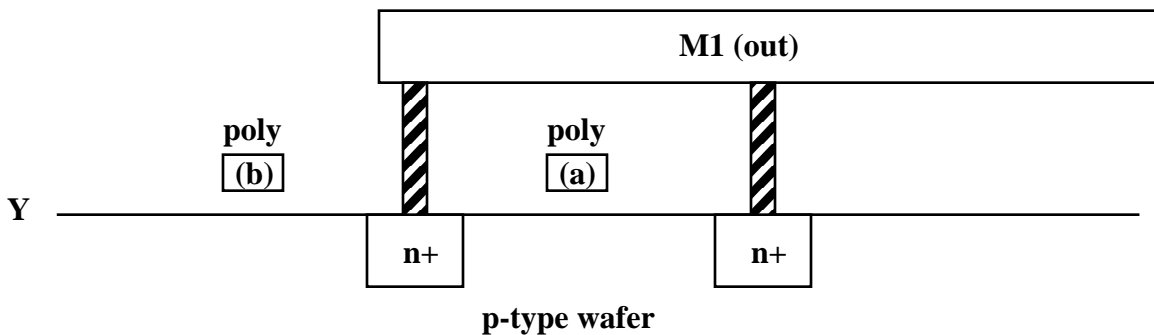
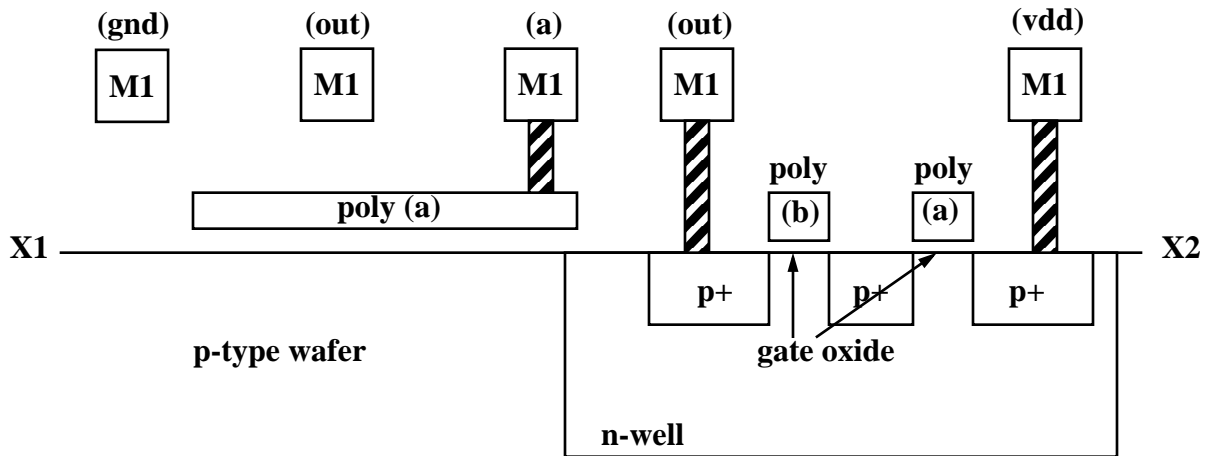
some equivalent solutions (there is more than one correct answer):



3. Provide a side-view diagram for each of the cuts X and Y through the layout below. Be sure to label each of the strata. Label your endpoints for the X cut, so it is clear which end is which.



solution:

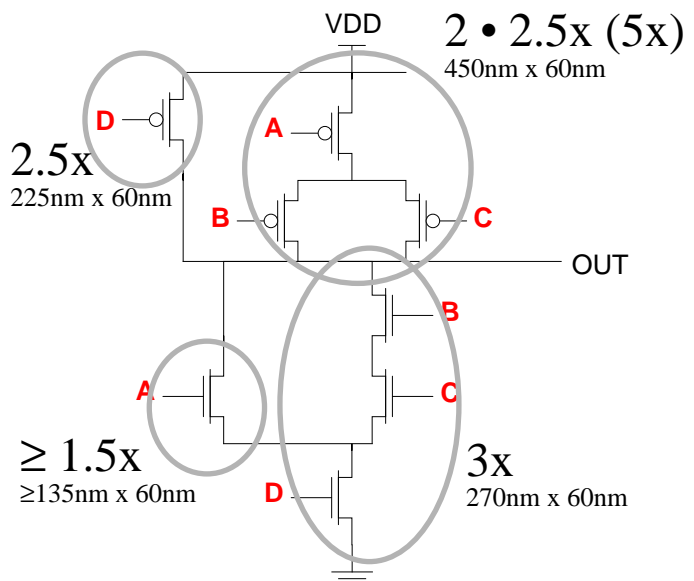
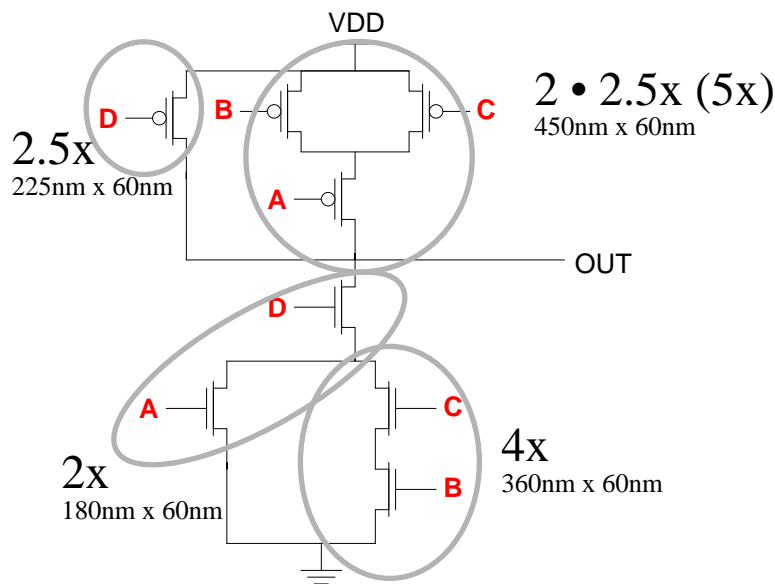


4. Consider the function $out = \sim((a + bc) \cdot d)$. Draw the circuit and size the transistors: size all NMOS and PMOS transistors so that the PUN and PDN each has equivalent resistance to a minimum-sized MOSFET, and then take into account the fact that $\mu_n = r \cdot \mu_p$ where $r = 2.5$ (i.e. the resistance of a unit PMOS device is 2.5 times that of a unit NMOS device).

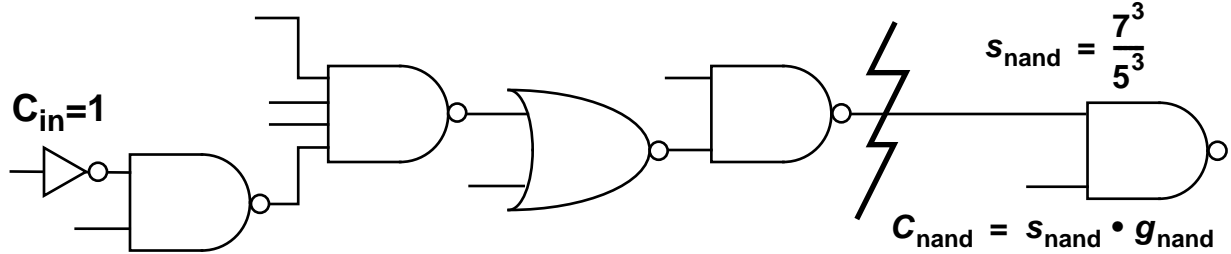
Important: Assume the circuit is implemented in a 60nm technology and that the dimensions of a minimum-sized MOSFET in this technology are **90nm width x 60nm length**. Express the dimensions of each MOSFET in the optimized circuit in nanometers (W nm x L nm). I.e., what is it that you are scaling?

some equivalent solutions (there is more than one correct answer):

min. device: $W \times L = 90\text{nm} \times 60\text{nm}$



5. You have identified a critical path through a circuit, as shown below. Consider the path up to the jagged line; the 2-input NAND beyond simply represents the load being driven (it can be thought of as the input to a D-latch, for example). That NAND has been scaled by a factor of $7^3 \div 5^3$ which can be approximated by the value 2.8. Thus, the load NAND has C_{nand} approximately equal to $3.5 C_{\text{in}}$. Find the scaling terms s_i for each gate and the optimized path delay. Assume that $\gamma=1$, that $r=3$, and that the p_i terms are all equal (leave as “p”).



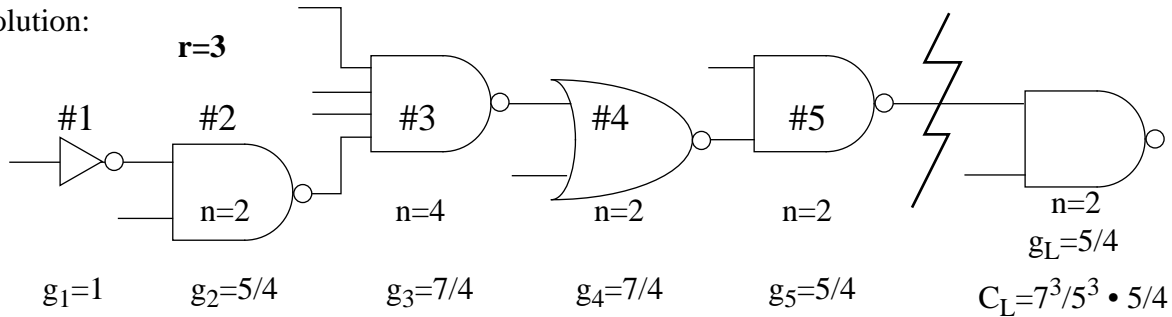
Equations you might find useful:

$$\text{Optimal gate effort } h = N\sqrt{GFB} = N\sqrt{H} \quad \text{Delay through path} = t_{p0} \sum \left(p_i + \frac{f_i g_i}{\gamma} \right)$$

$$g_{\text{nand}} = \frac{n+r}{1+r} \quad g_{\text{nor}} = \frac{1+nr}{1+r} \quad f_{i,\text{opt}} = \frac{h}{g_i} \quad \text{Optimal delay} = t_{p0} \left(\sum p_i + \frac{N\sqrt{H}}{\gamma} \right)$$

$$\text{Sizing for gate } i = \left(\frac{g_1 s_1}{g_i} \right) \prod_{j=1}^{i-1} \left(\frac{f_j}{b_j} \right) \quad F = \frac{C_{\text{load}}}{C_{\text{in}}} \quad G = \prod_i g_i$$

solution:



$$h = N\sqrt{GFB} = 5 \sqrt{\left(1 \cdot \frac{5}{4} \cdot \frac{7}{4} \cdot \frac{7}{4} \cdot \frac{5}{4} \right) \cdot \left(\frac{7^3 \cdot 5}{5^3 \cdot 4} \right)} = 5 \sqrt{\left(\frac{7^5 \cdot 5^3}{5^3 \cdot 4^5} \right)} = \frac{7}{4}$$

$$f_1 = \frac{7/4}{1} = 7/4 \quad f_2 = \frac{7/4}{5/4} = 7/5 \quad f_3 = \frac{7/4}{7/4} = 1 \quad f_4 = \frac{7/4}{7/4} = 1 \quad f_5 = \frac{7/4}{5/4} = 7/5 \quad \left(f_i = \frac{h}{g_i} \right)$$

$$s_1 = 1 \quad s_2 = \frac{1}{5/4} \cdot \frac{7}{4} = 7/5 \quad s_3 = \frac{1}{7/4} \cdot \frac{7}{4} \cdot \frac{7}{5} = 7/5 \quad s_4 = \frac{1}{7/4} \cdot \frac{7}{4} \cdot \frac{7}{5} \cdot 1 = 7/5 \quad s_5 = \frac{1}{5/4} \cdot \frac{7}{4} \cdot \frac{7}{5} \cdot 1 \cdot 1 = 49/25 \approx 2$$

$$\text{Delay} = t_{p0} \left(\sum p_i + \frac{N\sqrt{H}}{\gamma} \right) = t_{p0} \left(5p + \frac{35}{4} \right)$$